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(54) MANUFACTURE OF ELECTRODE WIRING OF SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: To reduce electric resistance of an Si gate electrode and a wiring by forming a metal film on a whole insulating film inclusive of a semiconductor layer having a pattern formed on it and forming an alloy layer composed of the metal film and the semiconductor layer.

CONSTITUTION: A pattern of a semiconductor layer 3 made of a poly-crystal Si is formed on an Si substrate 2 on which an insulating film 1 is provided. Next, an impurity diffused layer 4 is formed using the layer 3 as a mask. Next, a layer 11 is oxidized to leave layers 12 and 13. If, in this time, Mo is used as the metal and the whole is heat-treated in an oxidizing atmosphere, a metal part except the layers 12 and 13 are oxidized and the produced oxide is blown off and removed simply.